

# HS56021

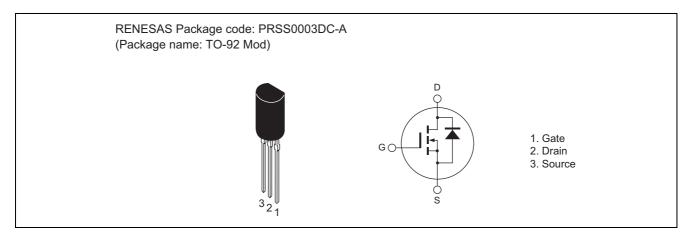
# Silicon N Channel MOS FET High Speed Power Switching

REJ03G1670-0200 Rev.2.00 Apr 24, 2008

### **Features**

- Low on-resistance
- Low drive current
- High density mounting

# **Outline**



# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

| Item  | Symbol                       | Ratings     | Unit |
|---|------------------------------|-------------|------|
| Drain to source voltage                     | V <sub>DSS</sub>             | 600         | V    |
| Gate to source voltage                      | V <sub>GSS</sub>             | ±30         | V    |
| Drain current                               | I <sub>D</sub>               | 0.2         | А    |
| Drain peak current                          | I <sub>D (pulse)</sub> Note1 | 0.8         | А    |
| Body-drain diode reverse drain current      | I <sub>DR</sub>              | 0.2         | А    |
| Body-drain diode reverse drain peak current | I <sub>DR</sub> (pulse)      | 0.8         | А    |
| Channel dissipation                         | Pch                          | 0.9         | W    |
| Channel to ambient thermal impedance        | $	heta_{ch-a}$               | 139         | °C/W |
| Channel temperature                         | Tch                          | 150         | °C   |
| Storage temperature                         | Tstg                         | -55 to +150 | °C   |

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

# **Electrical Characteristics**

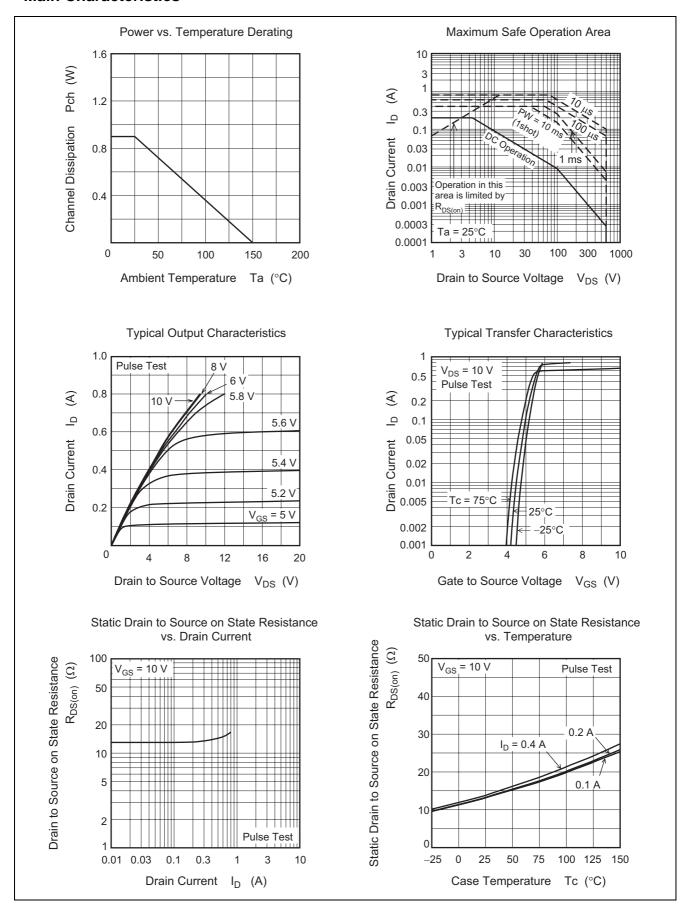
 $(Ta = 25^{\circ}C)$ 

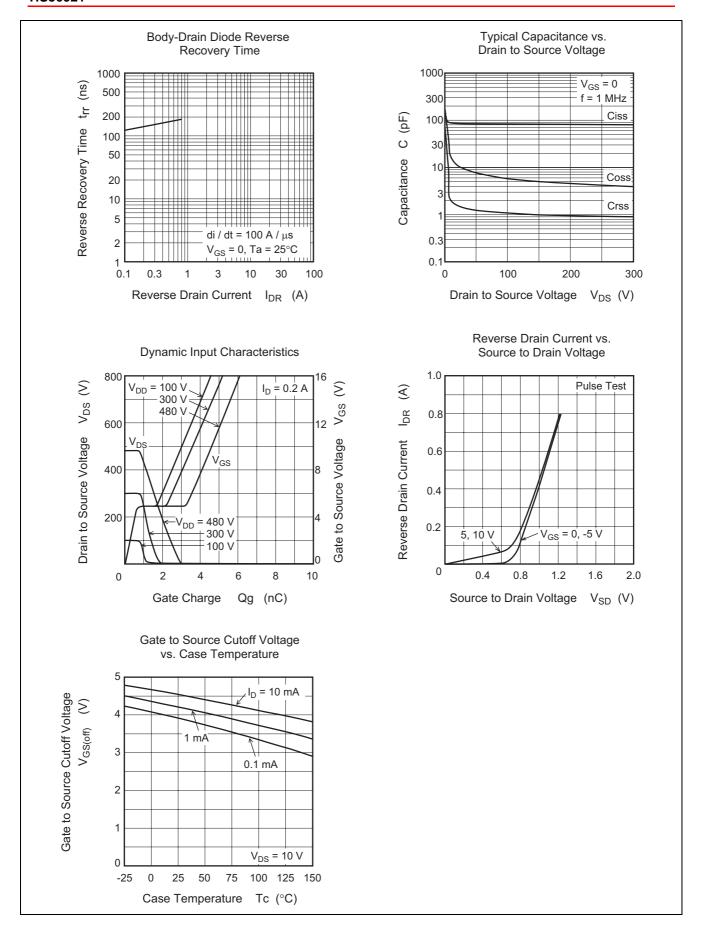
| Item                                       | Symbol              | Min | Тур  | Max  | Unit | Test conditions   |
|--|---------------------|-----|------|------|------|---|
| Drain to source breakdown voltage          | $V_{(BR)DSS}$       | 600 | _    | _    | V    | $I_D = 10 \text{ mA}, V_{GS} = 0$   |
| Zero gate voltage drain current            | I <sub>DSS</sub>    |     | _    | 1    | μΑ   | $V_{DS} = 600 \text{ V}, V_{GS} = 0$  |
| Gate to source leak current                | I <sub>GSS</sub>    |     | _    | ±0.1 | μΑ   | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$   |
| Gate to source cutoff voltage              | $V_{GS(off)}$       | 3   | _    | 5    | V    | $V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$   |
| Static drain to source on state resistance | R <sub>DS(on)</sub> | _   | 13   | 15   | Ω    | $I_D = 0.1 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note2}}$                                     |
| Input capacitance                          | Ciss                | _   | 84   | _    | pF   | V <sub>DS</sub> = 25 V  |
| Output capacitance                         | Coss                | _   | 11   | _    | pF   | $V_{GS} = 0$  |
| Reverse transfer capacitance               | Crss                | _   | 2    | _    | pF   | f = 1 MHz   |
| Turn-on delay time                         | t <sub>d(on)</sub>  | _   | 31   | _    | ns   | $I_D = 0.1 A$   |
| Rise time                                  | t <sub>r</sub>      | _   | 14   | _    | ns   | $\begin{aligned} V_{GS} &= 10 \text{ V} \\ R_L &= 3000 \Omega \\ Rg &= 10 \Omega \end{aligned}$ |
| Turn-off delay time                        | t <sub>d(off)</sub> | _   | 53   | _    | ns   |   |
| Fall time                                  | t <sub>f</sub>      | _   | 173  | _    | ns   |   |
| Total gate charge                          | Qg                  | _   | 4.5  | _    | nC   | V <sub>DD</sub> = 480 V   |
| Gate to source charge                      | Qgs                 | _   | 0.6  | _    | nC   | $V_{GS} = 10 \text{ V}$<br>$I_D = 0.2 \text{ A}$  |
| Gate to drain charge                       | Qgd                 | _   | 2.6  | _    | nC   |   |
| Body-drain diode forward voltage           | $V_{DF}$            | _   | 0.77 | 1.25 | V    | $I_F = 0.2 \text{ A}, V_{GS} = 0^{\text{Note2}}$  |
| Body-drain diode reverse recovery time     | t <sub>rr</sub>     |     | 150  | _    | ns   | $I_F = 0.2 \text{ A}, V_{GS} = 0$<br>$di_F/dt = 100 \text{ A}/\mu\text{s}$                      |

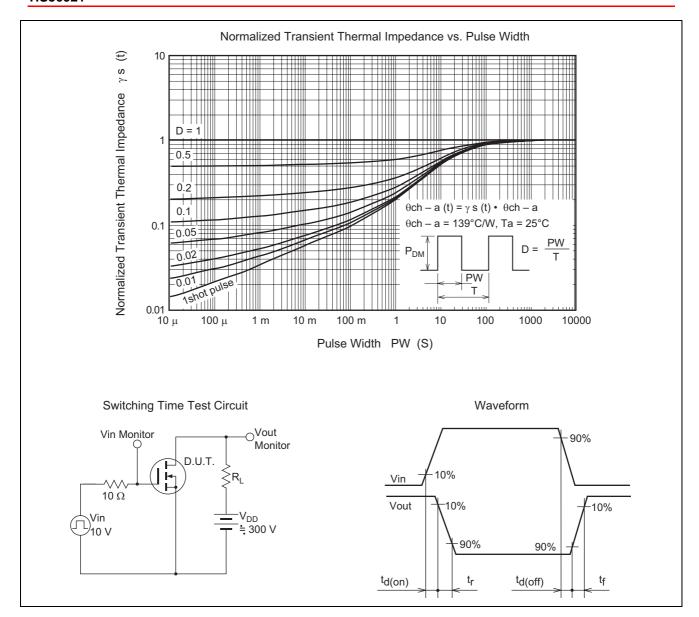
Notes: 2. Pulse test

<sup>3.</sup> Since this device is equipped with high voltage FET chip ( $V_{DSS} \ge 600 \text{ V}$ ), high voltage may be supplied. Therefore, please be sure to confirm about Electric discharge between Drain terminal and other terminal.

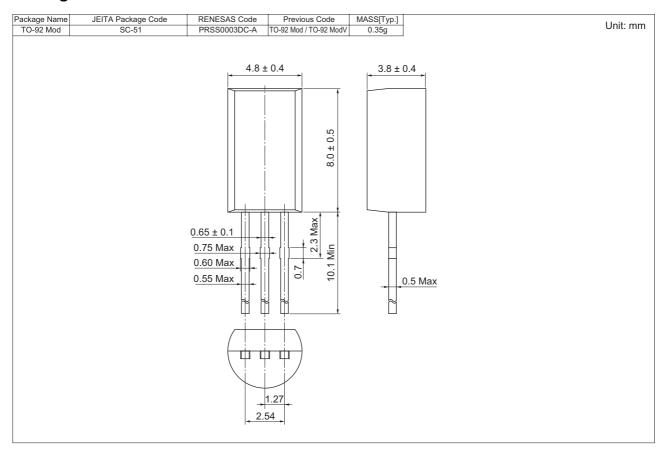
### **Main Characteristics**







# **Package Dimensions**



Since HS56021 is equipped with high voltage FET chip ( $V_{DSS} \ge 600 \text{ V}$ ), high voltage may be supplied. Therefore, please be sure to confirm about Electric discharge between Drain terminal and other terminal.

# **Ordering Information**

| Part No.    | Quantity | Shipping Container      |
|-------------|----------|-------------------------|
| HS56021TZ-E | 2500 pcs | Hold Box, Radial Taping |

Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

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### Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

**Renesas Technology Taiwan Co., Ltd.** 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510